

**isc Silicon PNP Power Transistor**
**2SA1444**
**DESCRIPTION**

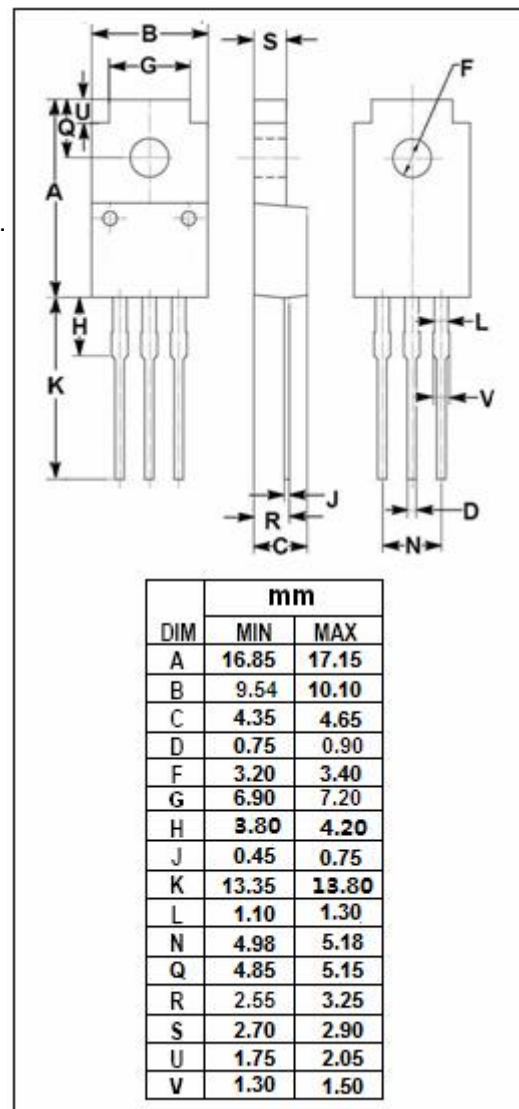
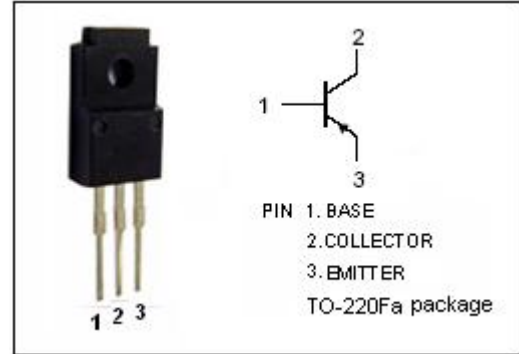
- Collector-Emitter Sustaining Voltage-  
:  $V_{CE(SUS)} = -60V(\text{Min})$
- High DC Current Gain-  
:  $h_{FE} = 100(\text{Min})@ (V_{CE} = -2V, I_C = -3A)$
- Low Saturation Voltage-  
:  $V_{CE(sat)} = -0.3V(\text{Max})@ (I_C = -8A, I_B = -0.4A)$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- This type of power transistor is developed for high-speed switching and features a high  $h_{FE}$  at low  $V_{CE(sat)}$ , which is ideal for use as a driver in DC/DC converters and actuators.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-7.0	V
$I_C$	Collector Current-Continuous	-15	A
$I_{CM}$	Collector Current-Pulse	-30	A
$I_B$	Base Current-Continuous	-7.5	A
$P_T$	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	30	W
	Total Power Dissipation @ $T_a = 25^\circ\text{C}$	2.0	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



## isc Silicon PNP Power Transistor

2SA1444

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -8.0A ; I <sub>B</sub> = -0.8A, L= 1mH	-60			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.4A			-0.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -12A; I <sub>B</sub> = -0.6A			-0.5	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.4A			-1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -12A; I <sub>B</sub> = -0.6A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -60V ; I <sub>E</sub> =0			-10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1.5A; V <sub>CE</sub> = -2V	100			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -2V	100		400	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -8A; V <sub>CE</sub> = -2V	60			

◆ h<sub>FE-2</sub> Classifications

M	L	K
100-200	150-300	200-400

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